

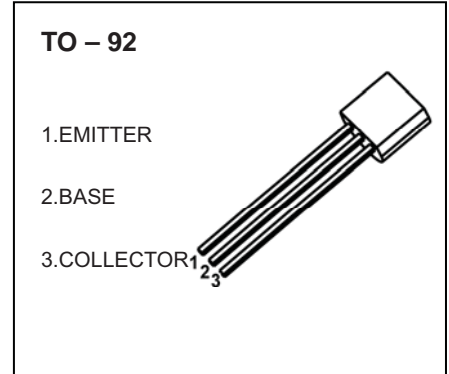


TO-92 Plastic-Encapsulate Transistors

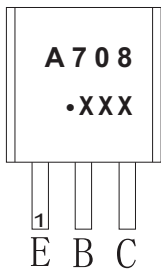
KSA708 TRANSISTOR (PNP)

FEATURES

- Low Saturation Medium Current Application

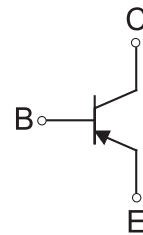


MARKING



A708=Device code
 Solid dot=Green molding compound device,
 if none,the normal device
 XXX=Code

Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSA708	TO-92	Bulk	1000pcs/Bag
KSA708-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-8	V
I _c	Collector Current -Continuous	-700	mA
P _D	Collector Power Dissipation	800	mW
R _{θJA}	Thermal Resistance rom Junction to Ambient	156.2	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1\text{mA}, I_E=0$	-80			V
Collector-emitter breakdown	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1\text{mA}, I_C=0$	-8			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-50\text{mA}$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.1	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		13		pF
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-50\text{mA}$		50		MHz

CLASSIFICATION OF h_{FE}

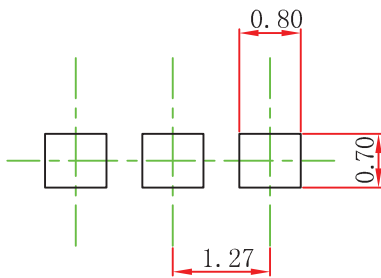
RANK	R	O	Y
RANGE	40-80	70-140	120-240

TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



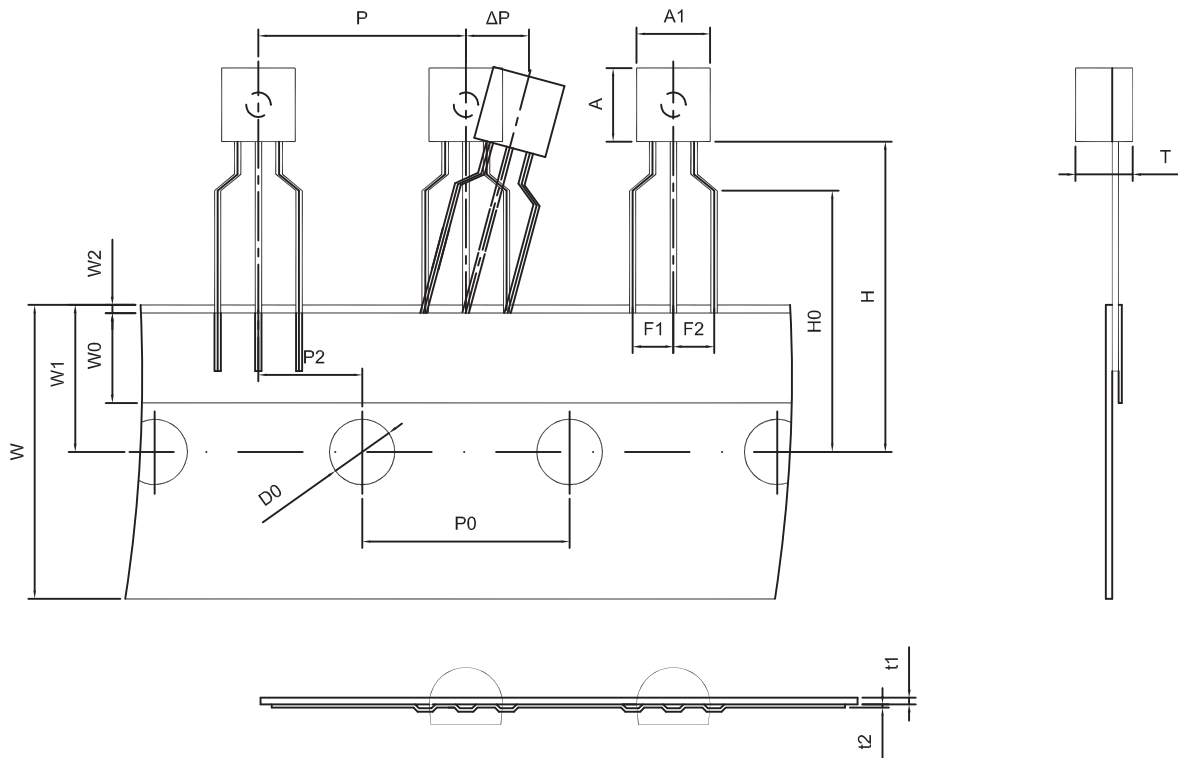
Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

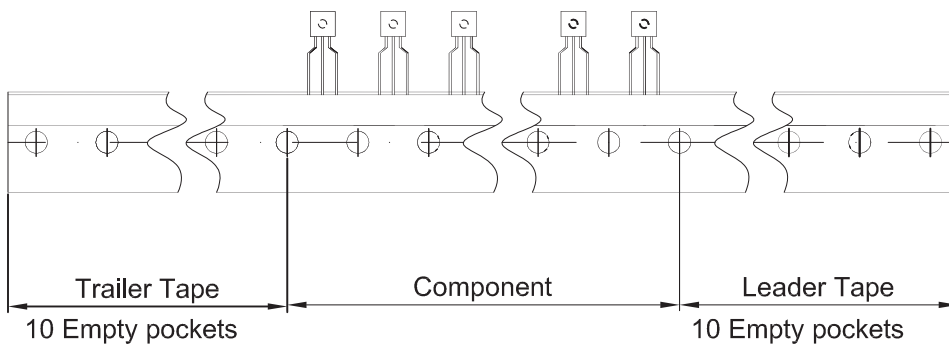
NOTICE

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TO-92 PACKAGE TAPING DIMENSION



Dimensions are in millimeter								
A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250

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